# MASTR Progress Line

66-88 MC RECEIVER MODELS 4ER40A16-27 ( WITH CHANNEL GUARD )



# **SPECIFICATIONS**

FCC Filing Designation

Frequency Range

Audio Output

Sensitivity

12-db SINAD (EIA Method) 20-db Quieting Method

Selectivity

EIA Two-Signal Method 20-db Quieting Method

Spurious Response

Frequency Stability

Modulation Acceptance

Squelch Sensitivity

Critical Squelch Maximum Squelch

Intermodulation (EIA)

Maximum Frequency Separation

Frequency Response

**ER-40-A** 

66-88 MC

2 watts at less than 10% distortion (using Speaker Model 4EZ16A10)

0.25 μν

0.4 µv

-85 db (adjacent channel, 30 KC channels)

-100 db at  $\pm 15$  KC

-100 db

 $\pm.0005\%$ 

±6 KC (narrow-band)

0.15 μν

Greater than 20 db quieting (less than 2 µv)

-60 db

0.4%

+1 and -8 db of a standard 6-db per octave de-emphasis curve from 300 to 3000 cps (1000-cps reference)

These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

TABLE OF CONTENTS												
SPECIFICATIONS	i											
DESCRIPTION	1											
CIRCUIT ANALYSIS	1											
RF Amplifier lst Oscillator and Multiplier Multiplier Selectivity Assembly lst Mixer and Crystal Filter 2nd Oscillator, 2nd Mixer and lst IF Amplifier 2nd IF Amplifiers and Limiters Discriminator lst Audio Amplifier Audio Amplifiers Squelch Channel Guard  MAINTENANCE  Disassembly	1 1 3 3 3 3 3 4 4 4 5 6											
Alignment Procedure	9 10											
Usable Sensitivity (12-db SINAD)	10 10 10											
	11											
	12											
SCHEMATIC DIAGRAM	13											
	14 & 15											
PRODUCTION CHANGES	16											
ILLUSTRATIONS												
Gigure l Block Diagram	2											
Tigure 2 Removing Top Cover	7											
igure 3 Removing Bottom Cover	7											
No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.												

#### **DESCRIPTION**

General Electric MASTR Progress Line Receiver Type ER-40-A is a double-conversion, superheterodyne FM receiver designed for operation on the 66-88 megacycle band.

The receiver is of single-unit construction and is completely housed in an aluminum casting for maximum shielding and rigidity. The top compartment of the casting contains the RF, oscillator, converter, high IF and 1st low IF amplifier stages. The bottom portion of the casting contains the audio squelch board and the optional Channel Guard board.

#### **CIRCUIT ANALYSIS**

The MASTR Progress Line Receiver is completely transistorized using a total of 18 silicon transistors. Input leads to the receiver are individually filtered by the 20-pin feed-through by-pass connector J443.

A regulated +10 volts is used for all receiver stages except the audio PA stage which operates from the 12-volt system supply.

Centralized metering jack J442 is provided for use with General Electric Test Set, Model 4EX3AlO, for ease of alignment and servicing. The Test Set meters the oscillator, multiplier, and limiter stages as well as the discriminator, audio PA, voice coil and regulated 10 volts.

#### RF AMPLIFIER (A343)

RF Amplifier (A343) consists of two high-Q helical resonators and an RF amplifier stage (Q1). The RF signal from the antenna is coupled by RF cable W441 to a tap on L347/L349. The tap is positioned to insure the proper impedance match to the antenna. RF energy is coupled through the two coils by an opening in the shield wall to the base of RF Amplifier Q1. The coils are tuned to the incoming frequency by air trimmer capacitors C343 and C344. The output of Q1 is coupled through three tuned circuits to the base of the first mixer.

#### 1ST OSCILLATOR AND MULTIPLIER (A358-A363)

The receiver 1st oscillator operates in a transistorized Colpitts oscillator circuit. The oscillator crystal operates in a fundamental mode at a frequency of approximately 15 to 20 megacycles. The crystal is cut to provide temperature compensation at the high end of the temperature range and is thermistor compensated at low temperatures. This provides  $\pm .0005\%$  frequency stability as soon as the receiver is energized -- without the warm-up time required by crystal ovens or warmers.

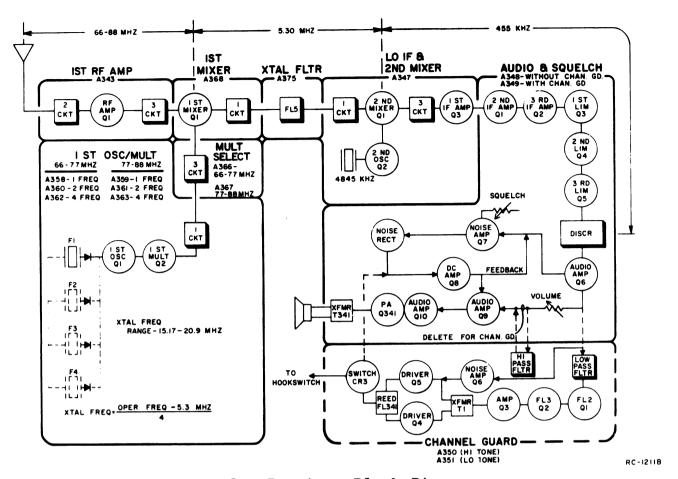


Figure 1 - Receiver Block Diagram

In single-frequency receivers, a jumper from P304 to C363 connects the regulated 10 volts to the crystal circuit, which forward biases diode CRl. Forward biasing the diode reduces its impedance, so that the crystal frequency is applied to the base of oscillator transistor Ql. Feedback for the oscillator is developed across C21/C22. The oscillator output is fed through C24 to the base of the 1st multiplier (Q2).

Multi-frequency receivers use only one oscillator transistor, and up to three additional crystal circuits, identical to the Fl crystal circuit, can be added. The 10-volt jumper is removed, and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the Control Unit.

The output of the 1st multiplier (quadrupler Q2) is transformer-coupled (T5/T6) to multiplier selectivity assembly A366/A367. The 1st multiplier tank is tuned to four times the crystal frequency.

The stage is metered at centralized metering jack J442-4 through metering network CR1, R1, C12 and C13.

#### MULTIPLIER SELECTIVITY ASSEMBLY (A366/A367)

Following the 1st multiplier tank (T5/T6) are three additional tuned circuits (A366/A367-L1, -L2 and -L3). Capacitor C10/C11 coupled the multiplier selectivity output to the base of the first mixer.

#### 1ST MIXER (A368) AND CRYSTAL FILTER (A346)

The RF signal from the RF Amplifier and the injection voltage from the 1st multiplier are applied to the base of 1st mixer A368-Q1. The mixer collector tank (L1 and C3) is tuned to 5.3 megacycles and provides impedance matching to the high IF filter.

The highly selective, two-stage crystal filter (FL5 and FL6) following the 1st mixer provides the major selectivity for the receiver. The output of the filter is fed through impedance matching transformer A347-Tl to the base of the 2nd mixer.

#### 2ND OSCILLATOR, 2ND MIXER AND 1ST IF AMPLIFIER (A347)

The 2nd oscillator A347-Q2 operates in a Colpitts oscillator circuit, with feedback supplied through C2. Crystal Yl maintains the oscillator frequency at 4845 KC. The low-side injection voltage is fed to the base of the 2nd mixer.

The Hi-IF signal from the filter is fed to the base of 2nd mixer Ql with the 2nd oscillator output. The 455 KC 2nd mixer output is fed to three tuned low IF circuits (L1, L2, L3). L1, L2 and L3 are required for shaping the nose of the IF waveform and provide some additional selectivity.

Capacitor Cl4 couples the low IF signal to the base of the lst low IF amplifier, A347-Q3. The output of Q3 is RC coupled to the base of the 2nd IF amplifier.

#### 2ND IF AMPLIFIERS AND LIMITERS (A349)

Following A347-Q3 are two additional RC coupled low IF amplifiers (A349-Q1 and -Q2). The 2nd IF amplifier stage is metered at J442-2 through metering network C8, CR1 and R12.

After the IF amplifiers are three RC coupled limiter stages (A349-Q3, -Q4 and -Q5). The 1st limiter is metered at J442-3 through metering network C13, CR2, R18 and C15.

#### DISCRIMINATOR (A349)

The receiver utilizes a Foster-Seely type discriminator. The output of the 3rd limiter is connected to a tap on the primary tuned circuit of discriminator Tl. This allows the discriminator to operate at a higher level. Diodes CR5 and CR6 rectify the 455 KC IF signals to recover the audio. The stage is metered at J442-10 through metering network R27 and C22.

#### 1ST AUDIO AMPLIFIER (A349)

The output of the discriminator is fed to the 1st audio amplifier (Q6). This stage operates as an emitter follower to match the impedance of the discriminator to the noise amplifier stage and VOLUME control. Q6 also provides some power gain.

#### AUDIO AMPLIFIERS

When audio is present in the incoming signal, it is taken off the emitter of Q6 and connected to the VOLUME control through A349-J9. The VOLUME control arm connects to A349-J8 which feeds the audio signal to the base of the 2nd audio amplifier, Q9. C34, C36, C37 and L4 make up the de-emphasis network. The collector current of Q9 should be adjusted to 650 milliamps by potentiometer R47 as indicated by a reading of 0.65 volts at metering jack J442-1. This adjustment should be made with the VOLUME control fully counterclockwise. Thermistor RT1 keeps the output current constant over wide variations in temperature after R47 has been set.

Following Q9 is a Darlington circuit, which consists of compound-connected transistors Q10 and Q341. The Darlington circuit provides a higher input impedance than is normally encountered in transistor amplifiers. Also, this circuit has a more linear operation, with less distortion at maximum power output.

The output of the amplifier stage is coupled by audio transformer T341 to the loudspeaker. Audio high and low are present at the centralized metering jack (J442). When the General Electric Test Set is connected to J442, these leads are connected to the black and green jacks for sensitivity, frequency response, distortion, power output and other measurements.

#### SQUELCH

Noise from audio amplifier Q6 is used to operate the squelch circuit. When no carrier is present in the receiver, noise is coupled to the base of noise amplifier Q7. The gain of the noise amplifier is determined by the SQUELCH control, which varies the bias on the base of Q7.

The noise amplifier output is fed through a high-pass filter (C30 and L1) which attenuates frequencies below 3 KC. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

Noise from the high-pass filter is rectified by CR3 and CR4, and the negative DC output of the noise rectifiers is fed to the base of DC amplifier Q8.

DC amplifier Q8 acts as a squelch switch. A negative output from the noise rectifiers cuts off the DC amplifier. When cut off, the collector is at the +10 volt supply potential. This positive voltage is fed to the base of Q9, a PNP transistor, cutting it off. Since audio stages Q9, Q10 and Q341 are DC coupled, Q10 and Q341 are cut off also.

The positive voltage from the collector circuit of the DC amplifier is used as feedback through R33 to the base of noise amplifier Q7, causing it to conduct more heavily. This feedback helps to sharply cut off Q8, providing sharp, rapid switching action.

When the receiver is quieted by a signal, noise voltage from the noise rectifiers is reduced and the DC amplifier conducts. While conducting, the collector potential of Q8 is negative and negative feedback to the base of noise amplifier Q7 causes it to conduct less.

This negative voltage is applied to the base of PNP transistor Q9 and causes it to conduct. Now, all the audio stages are turned on and sound is heard at the loudspeaker.

With the receiver squelched, the final audio amplifiers are cut off; and the receiver drain is less than 50 millamps in 12-volt systems.

It should be noted that a hysteresis effect was designed into the squelch circuit and, as a result, the squelch does not operate in the same manner as other conventional squelch circuits. The circuit is designed so that a weak signal will open the squelch. The signal may be reduced by 3 to 5 db without the squelch closing. This limits squelch "flutter" or "picket-fench" operation.

#### CHANNEL GUARD (A350/A351)

General Electric Channel Guard Decoder is designed to eliminate all calls that are not tone coded for the Channel Guard frequency. As long as the CHANNEL GUARD-OFF switch on the control unit is left in the CHANNEL GUARD position, all signals are locked out except those from transmitters that are continuously tone coded for positive identification by the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position instantly disables the Channel Guard operation so that all calls on the channel can be heard. When the hookswitch option is used, lifting the microphone from its hanger disables the Channel Guard Circuit.

#### Operation

Audio, tone and noise is picked up in the emitter circuit of Audio Amplifier A349-Q6 and is fed through A349-J9 to the VOLUME control and then to a high-pass filter (C20, C21, C22, C23 and L1) on the Channel Guard board through A349-J8, decoupling resistor R61 and A349-J12. The high-pass filter removes the tone from the audio signal, and the audio is then fed through A349-J13 to the base of Audio Amplifier A349-Q9.

To operate the Channel Guard Decoder, audio, tone and noise is picked up in the emitter circuit of A349-Q6 and is fed through A349-J18 to the base of the first low-pass filter stage (Q1) through a 250-cps band pass filter consisting of R1, R2, R3, C1, C2 and C3. Following Q1 is a second low-pass filter stage, Q2. The filter output is amplified by Q3 and coupled to the push-pull driver stage (Q4 and Q5) through T1.

Q4 and Q5 drive the reed decoder, FL341. Noise amplifier Q6 picks up and amplifies any high frequency (in the 5 KC range) and feeds it back to the driver stage to decrease the sensitivity of the reed and prevent noise pulsing.

FL341 is resonant at the correct tone frequency and the reed contacts open and close at the tone frequency. When the CHANNEL GUARD-OFF switch is in the CHANNEL GUARD position, the opening and closing of the reed contacts charges capacitor C19, which applies a limited current to the base of DC Amplifier A349-Q8. The receiver noise squelch circuit continues to operate normally until a carrier quiets the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position (or removing the microphone from its hanger in hookswitch options) opens the circuit to A350/A351-J5, which forward biases diode CR3. This causes current to flow in the circuit, bypassing the decoder reed (FL341). However, the receiver noise squelch circuit will operate until a carrier is received.

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If the Two-Way Radio is mounted on its side, rotate the decoder reed 90° in its mounting bracket so that the label showing the G-E Drawing and Part Number is facing the receiver heat sink. No change is required if the unit is mounted vertically. See Figure 3 for the location of the decoder reed and channel guard board.

#### **MAINTENANCE**

#### DISASSEMBLY

To service the receiver from the top --

- 1. Pull locking handle down and pull radio about one inch out of mounting frame.
- 2. Pry up cover at rear of receiver.
- 3. Slide cover back and lift off.

To service the receiver from the bottom --

- 1. Pull locking handle down and pull radio out of mounting frame.
- 2. Remove the screws in bottom cover and pry up cover at back of receiver.
- 3. Slide cover back and lift off.

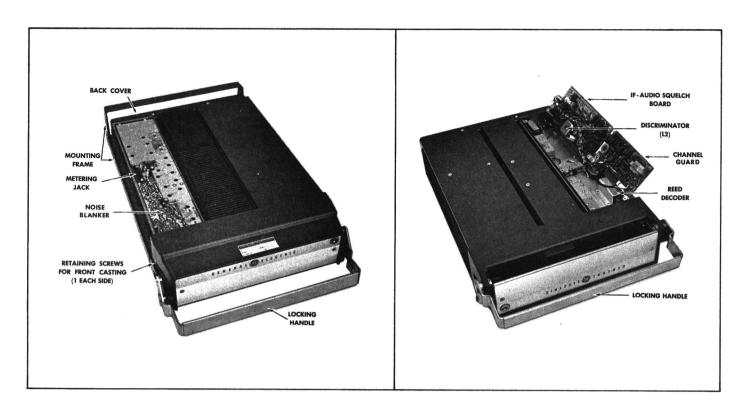


Figure 2 - Top Cover Removed

Figure 3 - Bottom Cover Removed

To remove the receiver from the system frame:

- 1. Loosen the two Phillips-head retaining screws in front casting (see Figure 2), and pull casting away from system frame.
- 2. Remove the four screws in the back cover.
- 3. Remove the two screws holding the receiver at each end of the system frame.
- 4. Disconnect the antenna jack and the 20-pin connector from the front of the receiver, and slide the unit out of the system frame.

#### FRONT END ALIGNMENT

#### EQUIPMENT REQUIRED

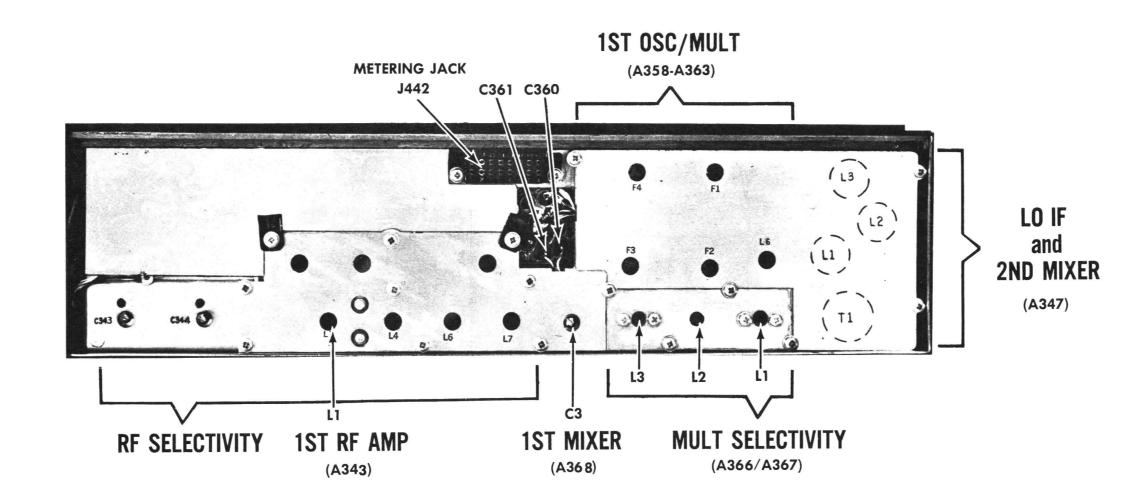
- G-E Test Set Model 4EX3A10, station Meter Switching Panel or 20,000 ohms-per-volt Multimeter with a l-volt scale.
- 2. A 455 KC and 66-88 MC signal source. Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.

#### PRELIMINARY CHECKS AND ADJUSTMENTS

- Connect Test Set Model 4EX3AlO to Receiver Centralized Metering Jack J442 and set meter sensitivity switch to the TEST 1 position.
- 2. With VOLUME control fully counterclockwise and Test Set in Position G, adjust R47 on IF-AUDIO & SQUELCH board for a reading of 0.65 volts. If using Multimeter, connect leads to J442-1 (AUDIO PA) and J442-8 (System Negative).
- 3. With Test Set in Position J, check for regulated +10 volts. If using Multimeter, measure from C360 to C361.
- 4. If using Multimeter, connect the positive lead to J442-16 (Ground).

#### ALIGNMENT PROCEDURE

	METERING POSITION		a a									
STEP	4EX3A10	MULTIMETER - at J442	TUNING CONTROL	METER READING	PROCEDURE							
			OSCILLAT	TOR/MULTIP	LIER							
1.	D (MULT-1)	Pin 4	L6 (on lst OSC/MULT and L1, L2, & L3 (on MULT SELECTIV- ITY)	See Pro- cedure	Tune L6 on 1st OSC/MULT and L1 on MULT SELECTIVITY for maximum meter reading. Next tune L2 for minimum meter reading. Then tune L3 for a maximum meter reading. Change voltage scale if necessary.							
	RF AMPLIFIER & SELECTIVITY											
2.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal adjacent to L7. Adjust the signal generator for discriminator zero.							
3.	B (2nd IF Amp)	Pin 2	L1 (1st RF Amp), L4, L6, L7, C343 and C344 (RF SELECTIV- ITY)	Maximum	Apply an on-frequency signal to antenna jack, keeping below saturation. Tune Ll, L4, L6, L7, C343 and C344 for maximum meter reading.							
4.	" "		L6 (lst OSC/MULT) and L1, L2, and L3 (MULT SELECTIVITY)	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune L6 on 1st OSC/MULT and L1, L2 and L3 on MULT SELECTIVITY for maximum meter reading.							
			FREQUEN	CY ADJUSTM	ENT							
5.	A (DISC)	Pin 10	C9 on 1st OSC (C10, C11 or C12 for multifrequency)	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.							



# J2 (L2 ON FAR SIDE) R47

IF-AUDIO & SQUELCH

LOOSEN CAPTIVE SCREWS

TO SWING BOARD OUT

#### COMPLETE RECEIVER ALIGNMENT

#### EQUIPMENT REQUIRED

- 1. G-E Test Set Model 4EX3AlO, station Meter Switching Panel or 20,000 ohms-per volt Multimeter with a 1-volt scale.
- 2. A 455 KC and 66-88 MC signal source. Connect a one-inch piece of insulated wire no larger than .065-inch diameter to generator output probe.
- 3. Two 33,000-ohm resistors for tuning low IF coils.\*

#### PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Connect Test Set Model 4EX3AlO to Receiver Centralized Metering Jack J442 and set meter sensitivity switch to the TEST 1 position.
- 2. Set crystal trimmer C9 to mid-capacity. In multi-frequency receivers, set C10, C11 or C12 to mid-capacity as required. Where the maximum frequency spacing is less than 200 KC, align the unit on channel F1. If the frequency spacing is greater than 200 KC, align the receiver on the center frequency.
- 3. With VOLUME control fully counterclockwise and Test Set in Position G, adjust R47 on IF-AUDIO & SQUELCH board for a reading of 0.65 volts. If using Multimeter, connect leads to J442-1 (AUDIO PA) and J442-8 (System Negative).
- 4. With Test Set in Position J, check for regulated +10 volts. If using Multimeter, measure from C360 to C361.
- 5. If using Multimeter, connect the positive lead to J442-16 (Ground).

#### ALIGNMENT PROCEDURE

-	112 1 211 11	G POSITION			
STEP	4EX3A10	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
					DISCRIMINATOR
1.	A (DISC)	Pin 10	L3 (Bottom slug on IF-AUDIO & SQUELCH board)	Zero	Apply a 455-KC signal to J2 on IF-AUDIO & SQUELCH board and adjust L3 (disc secondary) for zero meter reading.
2.	A (DISC)	Pin 10	L2 (top) and L3 (bottom slug on IF-AUDIO & SQUELCH board)	1.7 volts (2.1 v. maximum)	Loosen screws and swing IF-AUDIO & SQUELCH board open. Turn G-E Test Set to the TEST 3 position. Alternately apply a 445-KC and 465-KC signal while adjusting L2 and L3 for readings of at least 1.7 volts, but not more than 2.1 volts. Both readings must be within 0.1 volt.
3.	D (MULT-1)	Pin 4	L6 (on 1st OSC/ MULT) and L1, L2, L3 (on MULT SELECTIVITY)	See Pro- cedure	Tune L6 on 1st OSC/MULT and L1 on MULT SELECTIVITY for maximum meter reading. Next tune L2 for minimum meter reading. Then tune L3 for maximum meter reading. Change voltage scale if necessary.
					RF AMPLIFIER & SELECTIVITY
4.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal adjacent to L7. Adjust the signal generator for discriminator zero.
5.	B (2nd IF AMP)	Pin 2	L7, L6 and L4 (RF SELECTIVITY)	Maximum	Apply an on-frequency signal and tune for maximum meter reading as shown below, keeping signal below saturation.
	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,				Apply Signal Generator Probe To:         Tune:           L6         L7           L4         L6           L1         L4
6.	"		C343, C344 and L1 (1st RF AMP)	Maximum	Apply an on-frequency signal to the antenna jack. Tune C341, C342 and L1 for maximum meter reading, keeping signal below saturation.
7.	,,	"	L1 (1st RF AMP), L4, L6, L7, C343 and C344 (RF SELECTIVITY)	Maximum	Apply an on-frequency signal as above, keeping below saturation. Tune Ll, L4, L6, L7, C343 and C344 for maximum meter reading.
8.	,,	"	L6 (lst OSC/MULT) and L1, L2 and L3 (MULT SELECTIVITY)		Apply an on-frequency signal as above, keeping below saturation. Tune L6 (on lst OSC/MULT) and L1, L2 and L3 (on MULT SELECTIVITY) for maximum meter reading.
9.	"	"	C3 (1st MIXER)	Maximum	Apply an on-frequency signal as above, and tune C3 for maximum meter reading, keeping signal below saturation.
					LO IF & 2ND MIXER*
10.	B (2nd IF AMP)	Pin 2	T1 (2nd MIXER)	Maximum	Apply an on-frequency signal as above, and tune Tl for maximum meter reading, keeping signal below saturation.
11.	"	***	L1, L2 and L3 (LO IF)	Maximum	With one end of the 33,000-ohm resistors to ground, load and peak as follows: Load L2 at point B—Peak L1 and L3. Load L1 and L3 at Points A and C—Peak L2.
					FREQUENCY ADJUSTMENT
12.	A (DISC)	Pin 10	C9 on 1st OSC (C10, C11 or C12 for multi-frequency)	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.

\*NOTE — The low IF coils have been aligned at the factory and will normally require no further adjustment. If alignment is necessary refer to the RECEIVER OUTLINE DIAGRAM for location of resistor loading points A, B and C.

# ALIGNMENT PROCEDURE

LBI-3620

66—88 MHz MASTR RECEIVER MODELS 4ER40A16-27

Issue 2

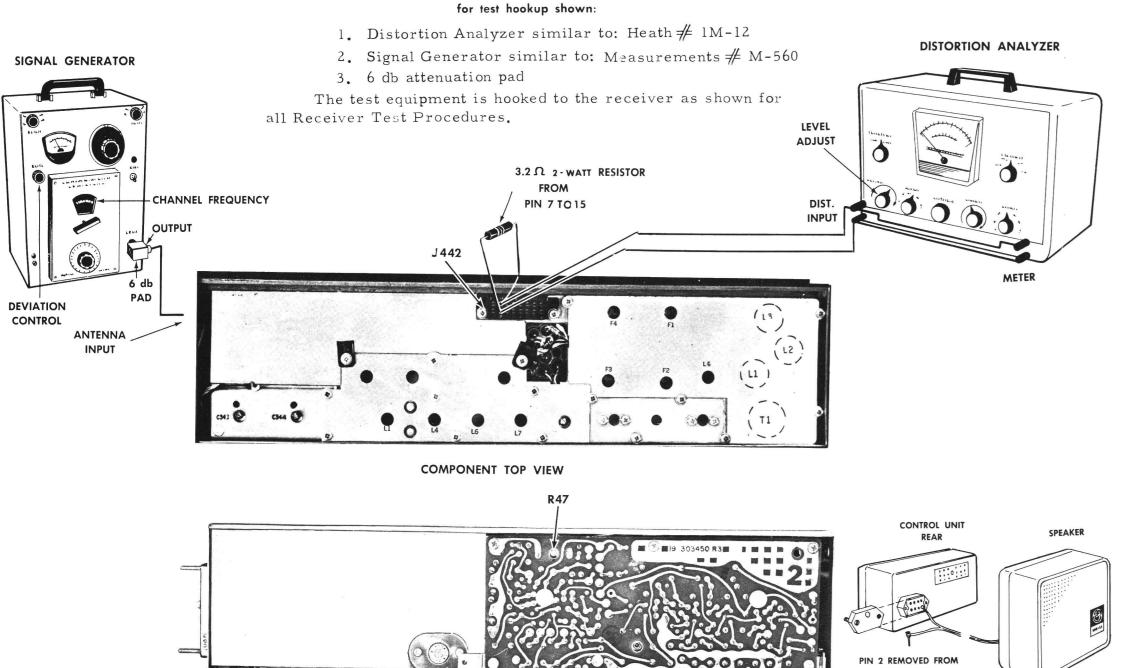
#### LBI-3620

# **TEST PROCEDURES**

a receiver that is operating---but not properly. The problems Check' listed to correct the problem. Additional corrective meaencountered could be low power, poor sensitivity, distortion, limi- sures are included in the Troubleshooting Procedure. Before ter not operating properly, and low gain. By following the sequence starting with the Receiver Test Procedures, be sure the receiver of test steps starting with Step 1, the defect can be quickly local- is tuned and aligned to the proper operating frequency.

These Test Procedures are designed to help you to service ized. Once the defective stage is pin-pointed, refer to the "Service

#### TEST EQUIPMENT REQUIRED



COMPONENT BOARD WIRING VIEW

STEP 1

# AUDIO POWER OUTPUT AND DISTORTION

#### **TEST PROCEDURE**

Measure Audio Power Output as follows:

- Connect a 1,000-microvolt test signal modulated by 1,000 cycles ±3.3 KC deviation to the antenna jack J441.
- Two-Watt Speaker:

When speaker is used disconnect speaker lead pin from J701-2 (on rear of Control Unit). Hook up a 3.2-ohm load resistor from J442-15 to J442-7

#### Handset:

When handset is used, lift handset off of hookswitch.

3. Two-Watt Speaker:

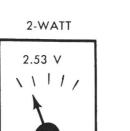
Connect Distortion Analyzer input across the 3.2-ohm resistor as shown

OR

#### Handset:

Connect Distortion Analyzer input from J442-15 to J442-7.

Two-watt speaker--set volume control for two-watt output (2.53 VRMS):



VOLTMETER SCALE ON DISTORTION ANALYZER

5. Make distortion measurements according to manufacturer's instructions. Reading should be less than 10% (5% is typical).

#### **SERVICE CHECK**

If the distortion is more than 10%, or maximum audio output is less than two watts (for two-watt speaker), make the following checks:

- 1. Battery and regulator voltage -- low voltage will cause distortion. (Refer to Receiver Schematic Diagram
- 2. Audio Bias Adjust (R47) -- should be adjusted for 0.65 volts. (Refer to Receiver Alignment on reverse side of page).
- 3. Audio Gain (Refer to Receiver Troubleshooting Procedure).
- 4. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

STEP 2

### **USABLE SENSITIVITY (12 db SINAD) TEST PROCEDURE**

Measure sensitivity of the receiver modulated at the standard test modulation as follows:

- 1. Be sure Test Step 1 checks out properly.
- 2. Reduce the Signal Generator output from setting in Test Step 1.
- Adjust Distortion Analyzer LEVEL control for a +2 db reading.
- Set CONTROL from LEVEL to DISTORTION reading. Repeat Steps 1, 2 and 3 until difference in reading is 12 db (+2 db to -10 db).
- 5. The 12-db difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. Reading should be less than 0.35 microvolts with audio output at least one watt (1.83 volts RMS across the 3.2-ohm receiver load).

#### SERVICE CHECK

If the sensitivity level is more than 0.35 microvolts, make the following checks:

- 1. Alignment of RF stages (Refer to RF Alignment in Receiver Alignment on reverse side of page.)
- 2. Gain measurements as shown on the Receiver Troubleshooting Procedure.

#### STEP 3

## MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH) TEST PROCEDURE

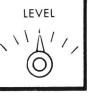
- 1. Be sure Test Steps 1 and 2 check out properly.
  - Set Signal Generator output for twice the microvolt reading obtained in Test Step 2 4.
- Increase Signal Generator frequency deviation.
- Adjust LEVEL Control for +2 db.

DB SCALE ON DISTORTION ANALYZER



5. Set CONTROL from LEVEL to DISTORTION reading. Repeat Steps 3, 4 and 5 until difference between readings becomes 12 db (from +2 db to -10 db).

> LEVEL DISTORTION ON DISTORTION ANALYZER



6. Deviation control reading for the 12-db difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ±6 KC (but less than ±9 KC).

#### STEP I - QUICK CHECKS

SYMPTOM	PROCEDURE									
NO SUPPLY VOLTAGE	Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.									
NO REGULATED 10 VOLTS	Check the 12-volt supply. Then check regulator circuit (See Troubleshooting Procedure for Power Supply).									
LOW 2ND LIM READING	Check supply voltages and then check oscillator reading at J442-4 as shown in STEP 2.									
	Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 2nd Limiter stages as shown in STEP 2.									
LOW OSCILLATOR READING	Check alignment of Oscillator (Refer to Front End Alignment Procedure).									
	Check voltage and resistance reading of 1st Oscillator/Multiplier Q1/Q2.									
	Check crystal Yl.									
LOW RECEIVER SENSITIVITY	Check Front End Alignment (Refer to Receiver Alignment Procedure).									
	Check antenna connections, cable and relay.									
	Check voltage and resistance readings of RF Amp and 1st and 2nd Mixers.									
	Make SIMPLIFIED GAIN CHECKS (STEP 2).									
LOW AUDIO	Check Audio PA (Q341) output current at J442-1. If reading is low									
	a. Refer to Receiver Alignment Procedure for BIAS ADJ.									
	b. Check Q341.									
	Check unsquelched voltage readings in Audio section (Refer to Receiver Schematic Diagram).									
	Check voltage and resistance readings on Channel Guard receiver.									
IMPROPER SQUELCH OPERATION	Check voltage and resistance readings of Squelch circuit (Refer to Receiver Schematic Diagram).									
DISCRIMINATOR IDLING TOO FAR OFF ZERO	See if discriminator zero is on 455 kHz.									

# STEP 3- VOLTAGE RATIO READINGS

#### EQUIPMENT REQUIRED:

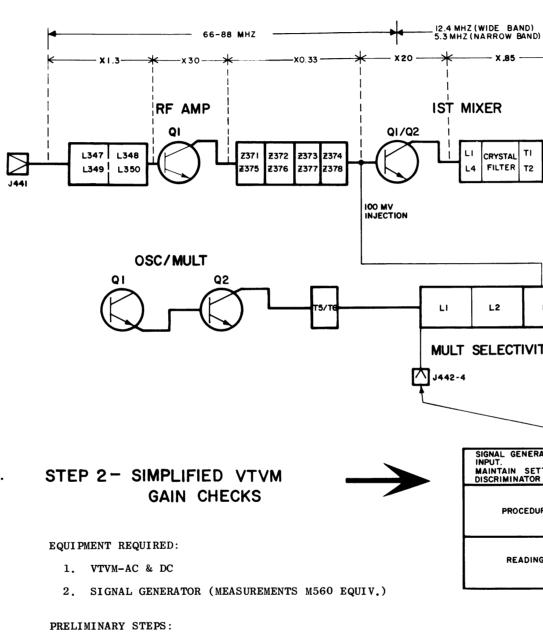
- 1. RF VOLTMETER (SIMILIAR TO BOONTON MODEL 91-CA OR MILLIVAC TYPE MV-18 C.
- 2. SIGNAL ON RECEIVER FREQUENCY (BELOW SATURATION).
  CORRECT FREQUENCY CAN BE DETERMINED BY ZEROING
  THE DISCRIMINATOR. USE 1,000 HERTZ SIGNAL WITH
  3.3 kHz (NB) or 10 kHz (WB) DEVIATION FOR AUDIO
  STAGE.

#### PROCEDURE:

- 1. APPLY PROBE TO INPUT OF STAGE (FOR EXAMPLE, BASE OF RF AMP). PEAK RESONANT CIRCUIT OF STAGE BEING MEASURED AND TAKE VOLTAGE READING  $(E_1)$ .
- 2. MOVE PROBE TO INPUT OF FOLLOWING STAGE (1ST MIXER\*). REPEAK FIRST RESONANT CIRCUIT THEN PEAK CIRCUIT BEING MEASURED AND TAKE READING (E2).
- 3. CONVERT READINGS BY MEANS OF THE FOLLOWING FORMULA.

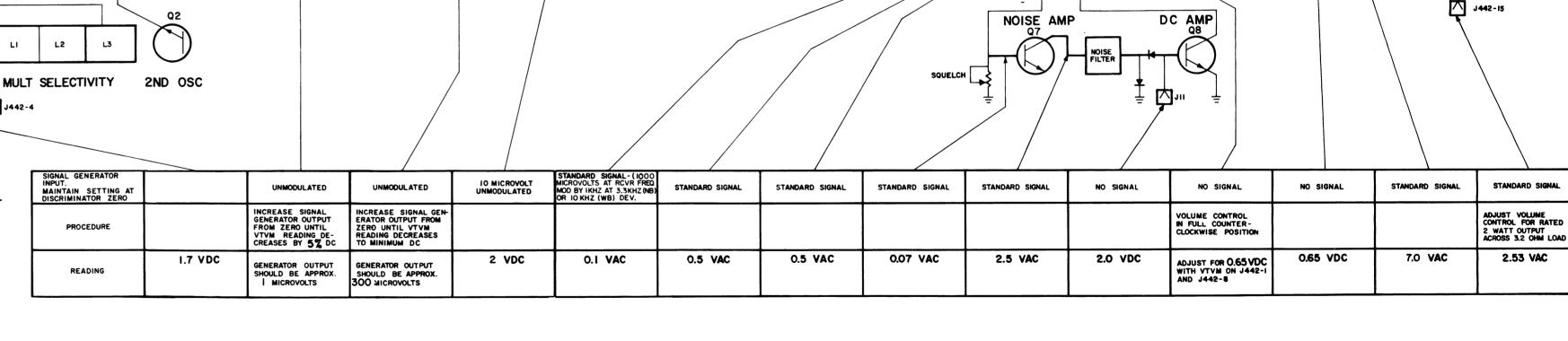
VOLTAGE RATIO = 
$$\frac{E_2}{E_1}$$

- 4. CHECK RESULTS WITH TYPICAL VOLTAGE RATIOS SHOWN ON DIAGRAM.
- \* NOTE: ON 1ST MIXER, REMOVE CRYSTAL BEFORE MEASURING BASE VOLTAGE. REPLACE CRYSTAL TO MEASURE COLLECTOR VOLTAGE.
  ON 2ND MIXER, INCREASE SIGNAL INPUT TO APPROX.
  0.3 V TO OVERRIDE INJECTION VOLTAGE.



IST IF AMP

COLLECTOR



IF - AUDIO - SQUELCH

DISC J7 J442-10

RC-1217B

#### 1. SET VOLUME CONTROL FULLY CLOCKWISE.

SET SQUELCH CONTROL FULLY COUNTERCLOCKWISE.

RECEIVER SHOULD BE PROPERLY ALIGNED.

4. CONNECT SIGNAL GENERATOR TO ANTENNA JACK.

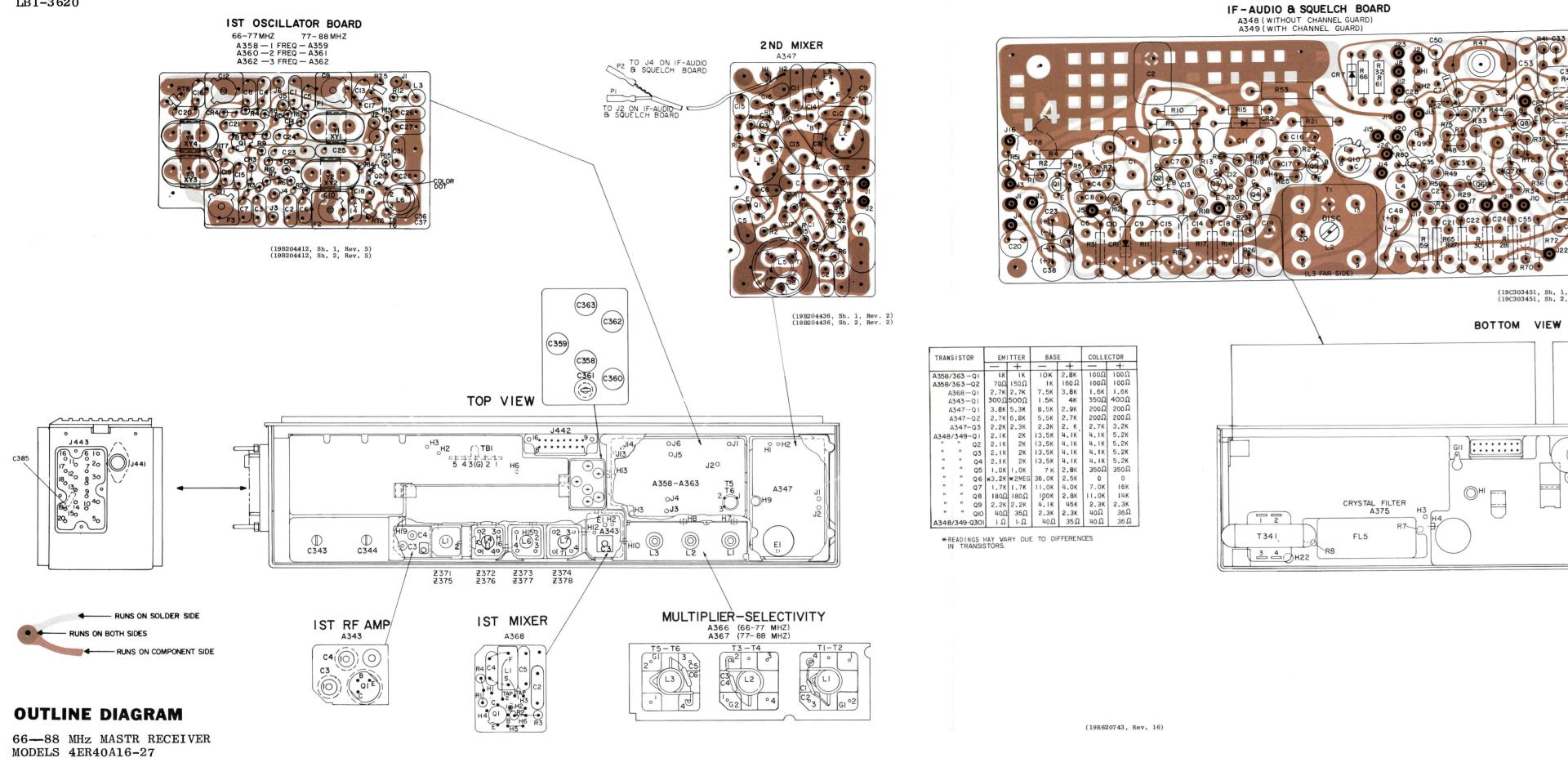
 VTVM CONNECTS BETWEEN GROUND AND POINTS INDICATED BY ARROWS.

# TROUBLESHOOTING PROCEDURE

66-88 MHz MASTR RECEIVER
MODELS 4ER40A16-27
(WITH CHANNEL GUARD)

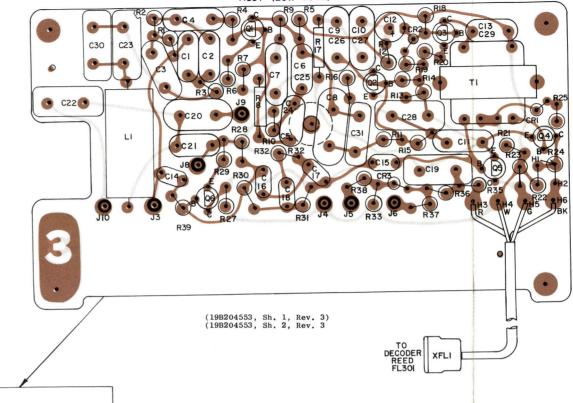
Issue 2

11





A350 (HI TONE) A351 (LOW TONE)



TRANSISTOR	EMI	TTER	В	ASE	COLLECTOR				
		+	_	+	1+	+			
01	56Ω	56Ω	8.3K	145Ω	6.5K	8.3K			
02	270 \O	270Ω	8K	500Ω	5K	5.5			
Q3	IK	IK	75K	3K	IK	11			
04	0	0	14K	45Ω	1 K	1 1 1			
05	0	0	14K	45Ω	IK	11			
Q6	20Ω	20Ω	4.5K	85Ω	2K	21			

# RESISTANCE READINGS

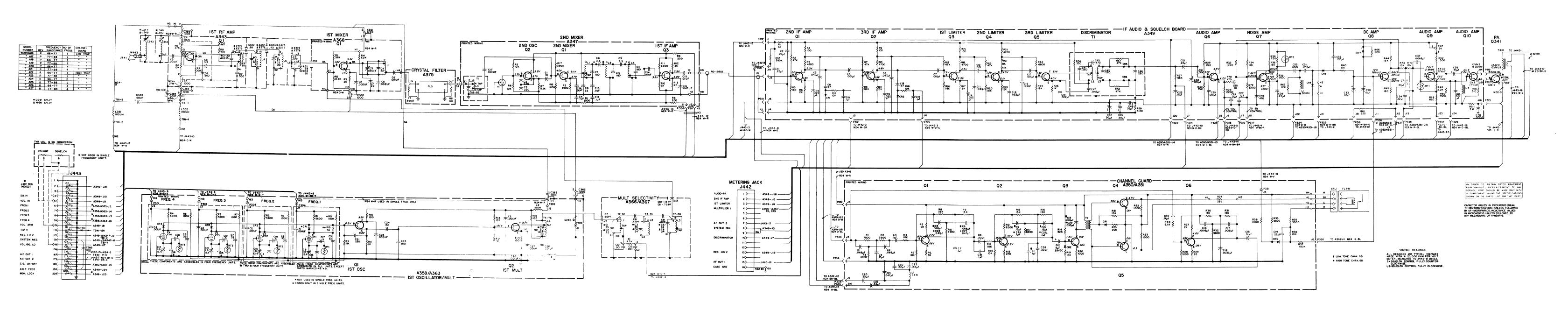
ALL READINGS ARE TYPICAL READINGS MEASURED WITH A 20,000 OHM-PER-VOLT METER, AND WITH CONTROL CABLE DISCONNECTED (OR IN STATIONS, PLUG TO J443 DISCONNECTED), READINGS ARE MADE WITH A SHORTING JUMPER CON-NECTED FROM C311-1 (+12V) TO C312-1 (-12), AND ARE MEASURED FROM TRAN-SISTOR PINS TO C311-1. + OR - SIGNS SHOW METER LEAD TO C311-1. CAUTION -

ALWAYS REMOVE THE SHORTING JUMP-ER AFTER MAKING RESISTANCE READ-INGS. APPLYING POWER WITH THE SHORTING JUMPER CONNECTED MAY DAMAGE THE UNIT

FOR READINGS OF: USE SCALE 1-100Ω X I 100-1K Ω X 10 1K-50K Ω X 1,000 50K Ω X 100,000

50 K Ω

Issue 3



(19R620722, Rev. 29)

# SCHEMATIC DIAGRAM

66-88 MHz MASTR RECEIVER
MODELS 4ER40A16-27
(WITH CHANNEL GUARD)

PARTS LIST LBI-3620 LBI-3637B 66-88 MHz RECEIVER WITH CHANNEL GUARD MODELS 4ER40A16 - 4ER40A27 19E500809G61-G72 GE PART NO. 5493392P7 C5 5494481P12 C6 7484398P4 484398P4 C8\* 5491601P130 4038642P1 19A115342P1 3R152P273I 3R152P103K 3R152P102K 3R152P471K 3R152P302K XQ1 5490277P5 Bandpass filter 19C304094G4 3R152P102K

DESCRIPTION RF AMPLIFIER ASSEMBLY - - - - - - - - CAPACITORS - - - - - -Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C. Ceramic disc: 1000 pf  $\pm$ 10%, 1000 VDCW; sim to RMC Type JF Discap. Silver mica: 500 pf ±10%, 500 VDCW; sim to Underwood Type J-1-HF. Deleted by REV L. Phenolic: 3.3 pf ±5%, 500 VDCW; sim to Quality - - - - - DIODES AND RECTIFIERS - - - - -- - - - - - - TRANSISTORS - - - - - - -- - - - - - - - RESISTORS - - - - - - - mposition: 27,000 ohms ±10%, 1/4 w. Composition: 10,000 ohms ±10%, 1/4 w. Composition: 1000 ohms ±10%, 1/4 w. omposition: 470 ohms ±10%, 1/4 w. Deleted by Composition: 3000 ohms ±10%, 1/4 w. Deleted by - - - - - - - SOCKETS - - - - - - -Transistor, phen: 3 contacts; sim to Alcon CRYSTAL FILTER ASSEMBLY (Deleted by REV C). - - - - - - - - - FILTERS - - - - - - -Composition: 4300 ohms ±10%, 1/4 w. Composition: 1000 ohms ±10%, 1/4 w. - - - - - - - - CAPACITORS - - - - - -Silver mica: 18 pf  $\pm 5\%$ , 500 VDCW; sim to Electro Motive Type DM-15. Polyester: 0.1 µf ±20%, 50 VDCW. 19A116080P7 In REV E and earlier: Polyester: 0.1 µf ±20%, 50 VDCW. 5491189P106

DESCRIPTION DESCRIPTION SYMBOL | GE PART NO. SYMBOL | GE PART NO. (Part of T1). Added by REV F. C5\* 19A116080P4 Polyester: 0.033 µf ±20%, 50 VDCW. Deleted by (Part of Tl), Deleted by REV F In REV E and earlier: - - - - - - - - PLUGS - - - - - - - -5491189P103 Polyester: 0.033 uf ±20%, 50 VDCW. P1 Contact, electrical; sim to Amp 42827-2. 5496219P47 Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef 4029840P1 Contact, electrical; sim to Amp 41854. C7\* 5496219P369 Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM. ----- TRANSISTORS -----19A115245P1 Silicon, NPN. Ceramic disc: 130 pf ±5%, 500 VDCW, temp coef -330 PPM. 5496219P566 **Q2** 19A115889P1 Silicon, NPN; sim to Type 2N2712. 19A115123P1 Silicon, NPN; sim to Type 2N2712. In REV D and earlier: Ceramic disc: 130 pf  $\pm 5\%$ , 500 VDCW, temp coef -470 PPM. 5496219P666 ----- RESISTORS -----Composition: 1500 ohms ±10%, 1/4 w. 5491601P140 Phenolic: 3.6 pf ±5%, 500 VDCW. R2 3R152P392K Composition: 3900 ohms ±10%, 1/4 w. In REV E and earlier: 3R152P103K Composition: 10,000 ohms ±10%, 1/4 w. 5491601P28 Phenolic: 2.7 pf ±5%, 500 VDCW. Ceramic disc: 180 pf  $\pm 5\%$ , 500 VDCW, temp coef -150 PPM. 5496219P369 3R152P512J Composition: 5100 ohms ±5%, 1/4 w. Composition: 200 ohms ±5%, 1/4 w. Ceramic disc: 130 pf ±5%, 500 VDCW, temp coef -330 PPM. 5496219P566 3R152P302J Composition: 3000 ohms ±5%, 1/4 w. In REV D and earlier: R11 Composition: 6200 ohms ±5%, 1/4 w. Ceramic disc: 130 pf ±5%, 500 VDCW, temp coef -470 PPM. R12 3R152P302J Composition: 3000 ohms ±5%, 1/4 w. 3R152P202J C12\* 19A116080P7 Polyester: 0.1 µf ±20%, 50 VDCW R15\* 3R152P153K Composition: 15,000 ohms ±10%, 1/4 w. Deleted In REV E and earlier: Polyester: 0.1 µf ±20%, 50 VDCW. R16 3R152P104K Composition: 0.1 megohm ±10%, 1/4 w. 5491189P106 Compositin: 0.39 megohm ±10%, 1/4 w. C14\* 19A116080P1 Polyester: 0.01 µf ±20%, 50 VDCW. In REV E and earlier: Polyester: 0.01 µf ±20%, 50 VDCW. 5491189P101 C16\* 19A116080P5 Polyester: 0.047 µf ±20%, 50 VDCW. - - - - - - - - CAPACITORS - - - - - - -In REV E and earlier: Ceramic disc: 82 pf ±5%, 500 VDCW, temp coef -80 PPM. C18 19C301540P261 Polyester: 0.047 µf ±20%, 50 VDCW. ----- MISCELLANEOUS -----5494481P112 Ceramic disc: 1000 pf  $\pm 20\%$ , 1000 VDCW; sim to RMC Type JF Discap. C26\* 19A116080P1 Polyester: 0.01  $\mu f$  ±20%, 50 VDCW. Added by REV J - - - - - - - - - CRYSTALS - - - - - - - -Quartz: freq 4845 KHz ±100 Hz at 25°C, temp range -30° to +75°C. 19A110192P3 4038104P1 Lug: solder dipped brass. IF/AUDIO ASSEMBLY - - - - - JACKS AND RECEPTACLES - - - - - -Contact, electrical: sim to Bead Chain L93-3. 4033513P4 - - - - - - - - CAPACITORS - - - - - - -19A115028P116 Polyester: 0.22 µf ±20%, 200 VDCW, C2 19A116080P9 Polvester: 0.22 uf ±20%, 50 VDCW. Transformer, freq: 455 KHz; sim to Automatic Mfg EX12673. L1\* 19A115711P4 19A115028P111 Polyester: 0.047 µf ±20%, 200 VDCW. In REV E and earlier: C4 5494481P112 19C303464G1 Coil. Includes C5 19A115028P109 Polyester: 0.022 µf ±20%, 200 VDCW. uning slug. Transformer, freq: 455 KHz; sim to Automatic Mfg EX12672. 19A115028P111 Polyester: 0.047 µf ±20%, 200 VDCW. 19A115711P3 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. 5494481P112 CR7 n REV E and earlier 5496219P717 Ceramic disc: 47 pf ±10%, 500 VDCW, temp coef Coil. Includes 19C303464G2 7160519P2 Tuning slug. Polyester: .022 µf ±20%, 200 VDCW. 19A115028P109 Transformer, freq: 455 KHz; sim to Automatic Mfg EX12674. L3\* 19A115711P5 C10 19A115028P114 Polyester: 0.1  $\mu$ f ±20%, 200 VDCW. C11 19A115028P111 Polyester: 0.047 µf ±20%, 200 VDCW. n REV E and earlier: Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to 19C303464G3 oil. Includes C12 5494481P112 7160519P2 Tuning slug.

SYMBOL | GE PART NO. SYMBOL | GE PART NO. DESCRIPTION Ceramic disc: 47 pf  $\pm 10\%$ , 500 VDCW, temp coef -750 PPM. C13 5496219P717 C14 19A115028P109 Polyester: 0.022 uf ±20%, 200 VDCW C15 19A115028P114 Polyester: 0.1 μf ±20%, 200 VDCW. Q1 19A115123P1 C16 5496219P421 Ceramic disc: 100 pf  $\pm 10\%$ , 500 VDCW, temp coef -220 PPM. C17 5494481P112 Ceramic disc: 1000 pf  $\pm$ 10%, 1000 VDCW; sim to RMC Type JF Discap. 19A115028P109 Polyester: 0.022 µf ±20%, 200 VDCW, C20\* 19A115680P103 Electrolytic: 20  $\mu f$  +150% -10%, 25 VDCW; sim to Mallory Type TT. Q6 Q8 Q9 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague C21 19A116080P9 Polyester: 0.22 µf ±20%, 50 VDCW. C22 19A115028P107 Polyester: 0.01 µf ±20%, 200 VDCW. C23 5491000P1 Electrolytic: 30 µf +75% -10%, 25 VDCW; sim to Sprague D25379. R2 19A115028P107 Polyester: 0.01 µf ±20%, 200 VDCW. Ceramic disc: 1000 pf  $\pm 10\%$ , 1000 VDCW; sim to RMC Type JF Discap. C25 5494481P112 R4 R5 Polyester: 0.1 µf ±20%, 50 VDCW. 19A116080P9 Polyester: 0.22 µf ±20%, 50 VDCW. C31 19A116080P5 Polyester: 0.047  $\mu f$  ±20%, 50 VDCW. C32 19A116080P9 Polyester: 0.22 µf ±20%, 50 VDCW C33 5496267P28 Tantalum: 0.47  $\mu f$   $\pm 20\%$ , 35 VDCW; sim to Sprague R10 C34 19A116080P9 Polyester: 0.22 μf ±20%, 50 VDCW. C35 5496267P6 Tantalum: 33 µf ±20%, 10 VDCW; sim to Sprague R12 19A115028P305 Polyester: 0.0068 µf ±10%, 200 VDCW, R13 Electrolytic: 100  $\mu f$  +150% -10%, 15 VDCW; sim to Mallory Type TT. C38 19A115680P107 R15 Silver mica: 470 pf  $\pm 10\%$ , 300 VDCW; sim to Electro Motive Type DM-15. 5490008P143 R16 C48 5495670P9 Electrolytic: 35 µf +75% -10%, 15 VDCW; sim to Sprague 30D. 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague R19 Silver mica: 2200 pf  $\pm 5\%$ , 500 VDCW; sim to Electro Motive Type DM-20. C52 4029003P16 19A115028P315 Polyester: 0.15 µf ±10%, 200 VDCW. R23 Polyester: 0.01 µf ±20%, 50 VDCW. 19A116080P1 C71\* 5496267P28 R25 Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C78\* 5494481P114 R27 R28 - - - - DIODES AND RECTIFIERS - - - - -4038056P1 19A115250P1 R34 R36 19A115250P1 R37 - - - - - JACKS AND RECEPTACLES - - - - -Contact, electrical: sim to Bead Chain L93-3. 4033513P4 R40 3R77P113J Choke, Includes: L1 4031476G1 7773023P25

5491736P6

19A115552P1

19A115123P1

19A115889P1

19A115123P1

19A115247P1

19A115300P1

3R77P330K

3R77P473K

3R77P183J

3R77P101K

3R77P472K

3R77P473K

3R77P183J

3R77P101K

3R77P472K

3R77P202J

3R77P103K

3R77P473K

3R77P101K

3R77P472K

3R77P202J

3R77P103K

3R77P473K

3R77P183J

3R77P472K

3R77P202J

3R77P682K

3R77P183J

3R77P102J

3R77P683K

3R77P222J

3R77P753J

3R77P512J

3R77P113J

3R77P153K

3R77P222J

3877P751J

. 3R77P562J

3R77P153K

Silicon, NPN.

In REV D and earlier:

DESCRIPTION Choke: 3.5 mh  $\pm 10\%$ , 2.5 ohms DC res max; sim to Silicon, NPN; sim to Type 2N2712. Silicon, NPN; sim to Type 2N2712 Silicon, NPN; sim to Type 2N2712 ilicon, NPN; sim to Type 2N2712 Silicon, NPN; sim to Type 2N2712 Silicon, NPN; sim to Type 2N1024. Silicon, NPN; sim to Type 2N3053 - - - - - - - - RESISTORS - - - - - - omposition: 33 ohms ±10%, 1/2 w Composition:  $47.000 \text{ ohms } \pm 10\%$ . 1/2 w. Composition: 18,000 ohms  $\pm 5\%$ , 1/2 w. Composition: 100 ohms ±10%, 1/2 w. Composition: 4700 ohms  $\pm 10\%$ , 1/2 w. omposition: 2000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±10%, 1/2 w composition: 18,000 ohms ±5%, 1/2 w Composition: 100 ohms ±10%, 1/2 w. Composition:  $4700 \text{ ohms } \pm 10\%$ , 1/2 w. Composition: 2000 ohms ±5%, 1/2 w. Composition: 10,000 ohms  $\pm 10\%$ , 1/2 w. Composition: 47,000 ohms ±10%, 1/2 w Composition: 100 ohms ±10%, 1/2 w. Composition:  $4700 \text{ ohms } \pm 10\%$ . 1/2 w. Composition: 2000 ohms ±5%, 1/2 w. Composition: 10.000 ohms ±10%, 1/2 w. Composition: 47,000 ohms  $\pm 10\%$ , 1/2 w Composition: 4700 ohms ±10%, 1/2 w. Composition: 2000 ohms ±5%, 1/2 w. Composition:  $6800 \text{ ohms } \pm 10\%$ , 1/2 w. Composition: 18.000 ohms ±5%, 1/2 w. Composition: 68,000 ohms  $\pm 10\%$ , 1/2 w. Composition: 2200 ohms  $\pm 5\%$ , 1/2 w. Composition:  $75,000 \text{ ohms } \pm 5\%$ , 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Composition: 0.10 megohm ±10%, 1/2 w. Composition: 11.000 ohms  $\pm 5\%$ . 1/2 w. Composition: 15,000 ohms ±10%, 1/2 w. Composition: 2200 ohms ±5%, 1/2 w. Composition: 750 ohms ±5%, 1/2 w. Composition: 5600 ohms ±5%, 1/2 w. Composition: 11,000 ohms  $\pm 5\%$ , 1/2 w. Composition: 15,000 ohms  $\pm 10\%$ , 1/2 w.

SYMBOL | GE PART NO. DESCRIPTION SYMBOL GE PART NO. 3R77P181K Composition: 180 ohms  $\pm 10\%$ , 1/2 w. 19A116080P107 R46\* 3R77P333K Composition: 33,000 ohms  $\pm 10\%$ , 1/2 w. Deleted 19A116080P106 19B209115P1 Variable, carbon film: 5000 ohms ±20%, 0.15 w; sim to CTS Type UPE-70. 3R77P222J Composition: 2200 ohms  $\pm 5\%$ , 1/2 w. 19A116080P109 3R77P821K Composition: 820 ohms  $\pm 10\%$ , 1/2 w. 3R77P392K Composition: 3900 ohms ±10%, 1/2 w. 5491459P109 19B209022P15 Wirewound, phen: 1 ohm  $\pm 5\%$ , 2 w; sim to IRC 19A116080P108 3R77P152K Composition: 1500 ohms ±10%, 1/2 w. C11\* 19A116080P107 19A116278P444 Metal film: 0.28 megohm ±2%, 1/2 w. Composition: 5100 ohms  $\pm 5\%$ , 1/2 w. 5491459P109 3R77P222K Composition: 2200 ohms ±10%, 1/2 w. 5495670P14 R65 3R77P123K Composition: 12,000 ohms  $\pm 10\%$ , 1/2 w. R66 3R77P223K Composition: 22,000 ohms  $\pm 10\%$ , 1/2 w. C13 19A116080P106 R70 3R77P471J Composition: 470 ohms  $\pm 5\%$ , 1/2 w. 19A116080P101 3R77P332J Composition: 3300 ohms ±5%, 1/2 w. R74\* 3R77P153K C16 5491459P110 and C17 Composition: 15,000 ohms  $\pm 10\%$ , 1/2 w. Added by REV E. Composition: 18,000 ohms  $\pm 10\%$ , 1/2 w. Added by REV E. R75\* 3R77P183K C18 5491459P111 R80\* 3R152P511J Composition: 510 ohms  $\pm 5\%$ , 1/4 w. Added by 19A116080P109 5491459P109 RT1 19B209143P2 C20 19A116080P109 C21\* 19A116080P105 Rod: 850 ohms ±10% res, 1 w max; sim to Globar 5491459P104 19A116080P110 DISCRIMINATOR ASSEMBLY C23\* 19A116080P109 - - - - - - - - - CAPACITORS - - - - - - -5491459P112 C41 19B209196P1 Ceramic disc: 280 pf ±5%, 500 VDCW, temp coef -115 ±30 PPM. 19A116080P105 C45 7489162P43 Silver mica: 470 pf ±5%, 300 VDCW; sim to Electro Motive Type DM-15. 19A116080P107 Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. C46 7489162P35 C28\* 19A116080P109 C47 19A116080P5 Polyester: 0.047 µf ±20%, 50 VDCW. 19A116080P104 - - - - - DIODES AND RECTIFIERS - - - - -C30\* 19A116080P109 CR5 19A115250P1 C31\* 19A116080P107 L2 19A121532G1 Coil. Includes tuning slug 7160519P1 CR3 19A115250P1 - - - - - - - RESISTORS - - - - - - -R56 3R152P331J Composition: 330 ohms ±5%, 1/4 w. Composition: 47,000 ohms ±5%, 1/4 w. 4033513P4 4033513P4 CHANNEL GUARD
A350 19C3O355OG1 (4ER4OA16-21)
A351 19C3O355OG2 (4ER4OA22-27) - - - - - - - - CAPACITORS - - - - - - -19A115690P2 Ll\* 19A116080P106 Polyester: 0.068 µf ±10%, 50 VDCW 19B204554G 19A116080P108 Polyester: 0.15 μf ±10%, 50 VDCW.

DESCRIPTION SYMBOL | GE PART NO. Polyester: 0.1 μf ±10%, 50 VDCW. Polyester: 0.068 µf ±10%, 50 VDCW 19A115123P1 19A116080P107 Polyester: 0.1 μf ±10%, 50 VDCW Polyester: 0.22 µf ±10%, 50 VDCW. In REV G and earlier: Polyester: 0.33 μf ±10%, 50 VDCW. R3 3R77P472J Polyester: 0.15 \( \mu f \pm 10\%, 50 \) VDCW. 3R77P103J Polyester: 0.1 µf ±10%, 50 VDCW 3R77P560J In REV G and earlier: R7 3R77P103J Polyester: 0.33 µf ±10%, 50 VDCW. R8 3R77P153J Electrolytic: 5 μf +75% -10%, 25 VDCW; sim to Sprague 30D. R10 3R77P752J Polyester: 0.068 µf ±10%, 50 VDCW. R11 3R77P103J Polyester: 0.01 µf ±10%, 50 VDCW. R13 3R77P271J Polyester: 0.0015 µf ±10%, 50 VDCW 3R77P103J 3R77P153J Polyester: 0.0033 µf ±10%, 50 VDCW. Polyester: 0.22 µf ±10%, 50 VDCW. In REV G and earlier: R18 3R77P823J Polyester: 0.33 µf ±10%, 50 VDCW R19 3R77P123J Polyester: 0.22 µf ±10%, 50 VDCW R20 3R77P102J Polyester: 0.047 µf ±10%, 50 VDCW R21 3R77P153J n REV C and earlier: 3R77P102J Polyester: 0.068 uf ±10%, 50 VDCW. Polyester: 0.33 µf ±10%, 50 VDCW R24\* 3R77P331J Polyester: 0.22 µf ±10%, 50 VDCW In REV G and earlier: Polyester: 0.47 µf ±10%, 50 VDCW. R26\* 3R77P203J Polyester: 0.047 uf ±10%, 50 VDCW. R28 3R77P512J Polyester: 0.1 µf ±10%, 50 VDCW. R29 3R77P200J 3R77P153J Polyester: 0.22 µf ±10%, 50 VDCW. Added by REV H Polyester: 0.033 µf ±10%, 50 VDCW. 3R77P682J Polyester: 0.22 µf ±10%, 50 VDCW. Added by REV H Polyester: 0.1 µf ±10%, 50 VDCW. Added by REV H. R35 3R77P302J - - - - - - DIODES AND RECTIFIERS - - - -R36 3R77P204J R39\* 3R77P512J - - - - - JACKS AND RECEPTACLES - - - - -Contact, electrical: sim to Bead Chain L93-3. T1 5490525P2 Contact, electrical: sim to Bead Chain L93-3. Coil, RF: 1.4 HY ±5%, sim to Artted AC5910. XFL1 19A121920G2

omposition: 10,000 ohms ±5%, 1/2 w. Composition: 15,000 ohms  $\pm 5\%$ , 1/2 w. Composition: 8200 ohms ±5%, 1/2 w. Composition: 82,000 ohms  $\pm 5\%$ , 1/2 w. Composition: 12,000 ohms ±5%, 1/2 w. Composition: 1000 ohms +5% 1/2 w. Composition: 15,000 ohms  $\pm 5\%$ , 1/2 w. Composition: 1000 ohms ±5%, 1/2 w. Composition: 330 ohms  $\pm 5\%$ , 1/2 w. Added by Composition: 200 ohms ±5%, 1/2 w. Composition: 20,000 ohms ±5%, 1/2 w. Deleted by REV M. omposition: 2000 ohms ±5%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. omposition: 20 ohms ±5%, 1/2 w, Composition: 15,000 ohms  $\pm 5\%$ , 1/2 w. Composition: 6800 ohms ±5%, 1/2 w. Composition: 3000 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±5%, 1/2 w. Composition: 0.2 megohm  $\pm 5\%$ , 1/2 w. Composition: 1000 ohms ±5%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Added by Audio freq: 100 to 10,000 Hz, Pri: 35,000 ohms ±10% imp, 1200 ohms ±15% DC res, Sec 1: 2000 ohms imp, 250 ohms ±10% DC res, Sec 2: 2000 ohms imp, 250 ohms ±10% DC res. - - - - - - - - SOCKETS - - - - - - - - -Reed, mica-filled phen: 7 pins rated at 1 amp at 500 VRMS with 3-11/32 inches of cable.

DESCRIPTION

- - - - - - - - TRANSISTORS - - - - - -

----- RESISTORS -----

Silicon, NPN; sim to Type 2N2712.

Composition: 7500 ohms  $\pm 5\%$ , 1/2 w.

omposition: 4700 ohms  $\pm 5\%$ , 1/2 w.

Composition: 10.000 ohms +5% 1/2 w.

Composition: 56 ohms ±5%, 1/2 w.

Composition: 10,000 ohms  $\pm 5\%$ , 1/2 w.

Composition: 15,000 ohms  $\pm 5\%$ , 1/2 w.

Composition: 7500 ohms ±5%, 1/2 w.

Composition: 6200 ohms ±5%, 1/2 w

Composition: 270 ohms ±5%, 1/2 w.

Composition: 10,000 ohms ±5%, 1/2 w.

SYMBOL GE PAR	RT NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	L GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO	DESCRIPTION
SYMBOL GE PAR  A358 thru A363  C1 thru C4 C5 5496219P thru C12 C13 thru C16 C17 thru C20 C21 5496219P C23 5494481P C24 5490008P C25 5496219P C26 thru C28 C31 5494481P C24 5490008P C25 5494481P C28 C31 5494481P C38 C31 5494481P C19 C10 C10 C10 C10 C11 C10 C11 C11 C11 C11	P112 P751 P106 P40 85P93 P771 P114 P31 P467 P112 03P1 03P1 P4	DESCRIPTION	RT5 thru RT8  T5 and T6  C36  C37  L5  XY1 thru XY4  Y1 thru Y4  Y1 thru Y4  C8 and A367	GE PART NO.  198209284P7  5496218P250 5496218P246  19A121481P1  5491798P5  198206576P6  198206576P7  5491601P13  3R152P473K  3R152P392K	Disc: 62 ohms res nominal at 25°C, color code violet.	T3 and T4  C3  C4  C13  L2  T5 and T6  C5  C6  C10  C11  L3	5491798P5  5496218P252  5496218P248  5494481P11  19B204981P6  5491798P5  5496218P252  5496218P248  * 5491601P26  5491601P26  * 5491601P18  5491601P23  19B204548P6  5491798P5  5494481P114  5491271P106	COIL ASSEMBLY T3 19B204981G1 (48R40A16, 18, 20, 22, 24, 26) T4 19B204981G2 (4ER40A17, 19, 21, 23, 25, 27)	R1 R2 R3 R4 A375*  FL5  FL6*  R1* R2* R7* R8*  C352 C353 C358 C358 C358 C363 C383 C384*	3R152P563J 3R152P822J 3R152P202J 3R152P102J  19B206692G1  19C304094G4  19C304094G4  3R152P432K  3R152P102K  3R152P103K  19B206692G1  3R152P62ZJ  3R152P103K  5491601P117  5491601P112  5493392P7  5496267P11  19A115680P3	Composition: 56,000 ohms ±5%, 1/4 w. Composition: 8200 ohms ±5%, 1/4 w. Composition: 2000 ohms ±5%, 1/4 w. Composition: 1000 ohms ±5%, 1/4 w. Composition: 1000 ohms ±5%, 1/4 w.  CRYSTAL FILTER ASSEMBLY 19B204616G3	SYMBOL  J441  J442  J443  L347 thru L350  C343 and C344  L351 and L352  P304 thru P309 P310  P311 thru P320 P321  P325  P327 thru P337  Q341*	19C307140P885 19C307140P948 19C307140P1000 19C307140P1072 19C307140P1072 19C307140P1108 19C307140P1138 19C307140P1363 19C307140P1363 19C307140P1363 19C307140P1514 19C307140P1567 19C307140P1622 19C307140P1622 19C307140P1738 19C307140P1738 19C307140P1738 19C307140P1738 19C307140P1739 19C307140P1928 19C307140P1928 19C307140P2035  19B209122P1 19B205689G2 19C303426G1  19B209159P1 7488079P72 4029840P1 4029840P2 4029840P2 4029840P2 19A115527P1	88.5 Hz 94.8 Hz 100.0 Hz 103.5 Hz 107.2 Hz 114.8 Hz 119.9 Hz 114.8 Hz 123.0 Hz 127.3 Hz 131.8 Hz 131.8 Hz 131.8 Hz 141.3 Hz 141.3 Hz 146.2 Hz 151.4 Hz 151.4 Hz 165.7 Hz 179.9 Hz 179.9 Hz 179.9 Hz 179.9 Hz 179.9 Hz 179.9 Hz 179.8 Hz 179.2 Hz 179.2 Hz 186.2 Hz 192.8 Hz 203.5 Hz	TB1  W441  Z371  C1  C3  C4*  L1  R1*  R2*  Z372  C1  L1  Z373	GE PART NO.  7487424P7  5496218P247  5491601P17  5494481P7  19B204842P8  3R152P222K  3R152P222K  3R152P471K  5491798P5  5496218P249  19B204832P6  5496218P249		C5*  L7*  Z375  C2  C3  C4*  L1  R1*  R2*	GE PART NO.  5494481P13  19B204831P6  19A121564P1  5491798P5  5496218P244  5491601P17  5494481P7  19B204842P8  3R152P222K  3R152P222K  3R152P471K  5491798P5  5496218P246  19B204832P6  5496218P246	DESCRIPTION	C4* C5*  L7*  1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29	5496218P256 5494481P13	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM. Deleted by REV C.  Ceramic disc: 2000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Added by REV C.
R4  R5*  3R152P10  R6 thru R8  R9 3R152P10  R10 3R152P10  R11 and R12  R13 3R152P10  R14 3R152P10  R15 3R152P10  R19* 3R152P36	04K 53J 01K 02J 51J 03J	Composition: 0.1 megohm ±10%, 1/4 w. Deleted by REV A.  Composition: 0.1 megohm ±10%, 1/4 w.  Composition: 15,000 ohms ±5%, 1/4 w.  Composition: 1000 ohms ±10%, 1/4 w.  Composition: 1000 ohms ±5%, 1/4 w.  Composition: 150 ohms ±5%, 1/4 w.  Composition: 10,000 ohms ±5%, 1/4 w.  Composition: 100 ohms ±10%, 1/4 w.  Composition: 36 ohms ±5%, 1/4 w.  Composition: 36 ohms ±5%, 1/4 w.  Composition: 36 ohms ±5%, 1/4 w.	C1 C2 C7 C12	5496218P251 5496218P247 5491601P15 5494481P11 7777146P3 19N204822P7	T2 19B204822G2 (4ER40A17, 19, 21, 23, 25, 27)	C5	5494481P114 5494481P12 5496218P247 4038104P1 19A121082G1	coef -80 PPM.  Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to	C385*  CR301*  FL341	5496267P11 7774750P4 4037822P1 19C307140P670 19C307140P770 19C307140P770 19C307140P825	Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.  Ceramic disc: .001 µf +100% -0%, 500 VDCW. Added by REV B.  DIODES AND RECTIFIERS Silicon. Added to 4ER40A16-21 by REV N. Added to 4ER40A22-27 by REV P.  FILTERS Reed, detector: coil - 600 ohms ±10%, standard 7-pin tube socket mounting.  67.0 Hz 71.9 Hz 77.0 Hz	Q341*	19A115246P1	,	2374	19B204830P6 5491798P5 5496218P248 5496218P251 5496218P251	Coil.  COIL ASSEMBLY 19820483161 (Used in Models 4ER40A16, 18, 20, 22, 24, 26)  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.  In REV B and earlier: Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -80 PPM.  Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -80 PPM.  Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -80 PPM.  Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -80 PPM.  Deleted by REV C.	z378	19B204830P6  19B204830P6  5491798P5  5496218P245  5496218P256	-80 PPM.	28	19A121383P1	Support.

#### PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - To incorporate improved transistor and transformer; changed Q341 and T341. To simplify alignment; changed R1 on Multiplier Selectivity Board A366/A367. On single frequency units deleted CR1, R5 and added R19 on 1st Oscillator/Multiplier Board A358/A363.

REV. B - To eliminate feedback with receiver cabling. Added C385.

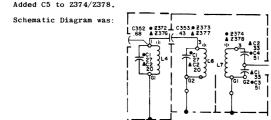
REV. C - To improve impedance matching to Crystal Filter.
Deleted A346 and added A375.

Changed C10 and C11 on A366/A367.

Changed Cl and Ll and deleted C2 on Z374.

Changed C3 and L7 and deleted C4 on Z378.

Added C5 to Z374/Z378.



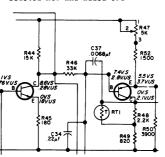
REV. D - To allow for variations in audio response. Changed C21 on A350/A351.

REV. E - To improve temperature compensation. Changed C7, C10 and C11 on A347.

To reduce variations in discriminator output. Changed Q4 and Q5 on A349.  $\,$ 

To reduce audio rumble. Deleted R46 and added C71 on A349.

Schematic Diagram was:



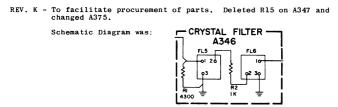
REV. F - To improve temperature characteristics. Changed C4, C5, C7, C8, C9, C10, C11, C12, C13, C14, C15, C16, L1, L2, L3, L4 and L5 on A347.

REV. G - To improve DC bias stability. Added R80 to A349.

REV. H - To facilitate the procurement of parts. Changed C8, C11, C19, C23 and L1 on A350/A351.

Added C28 on A350 and C30 and C31 to A350/A351.

REV. J - To reduce receiver lock-up. Replaced C5 with C26 on A347.



REV. L - To improve stability in RF amplifier. Deleted C7, C8, R8, and R9 on A343.

REV. M - 4ER40A22-27 To reduce falsing. Deleted R39 and added R24 on A351.

REV. M - 4ER40A16-21 Rev. N - <u>4ER40A22-27</u> To eliminate capacitor failures. Changed C20 on A349.

REV. N - 4ER40A16-21 REV. P -  $\frac{4\text{ER40A22-27}}{\text{To protect}}$  the output transistor. Added CR301.

REV. P -  $\frac{4ER40A16-21}{TO \ improve}$  PA stability. Added C78 to A349.

MAINTENANCE MANUAL

LBI-3620

MOBILE RADIO DEPARTMENT GENERAL ELECTRIC COMPANY • LYNCHBURG, VIRGINIA 24502

